

## 15A, 650V N-CHANNEL POWER MOSFET

### ■ DESCRIPTION

The UTC **15N65** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **15N65** is universally applied in active power factor correction and high efficient switched mode power supplies.

### ■ FEATURES

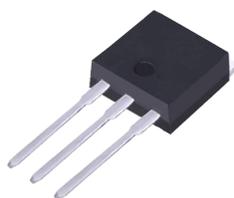
- \*  $R_{DS(ON)} \leq 0.65\Omega$  @  $V_{GS}=10V$ ,  $I_D=7.5A$
- \* High switching speed
- \* Improved dv/dt capability



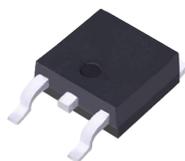
TO-220



TO-220F



TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS ( $T_c=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		$V_{DSS}$	650	V
Gate to Source Voltage		$V_{GSS}$	$\pm 30$	V
Continuous Drain Current	Continuous	$I_D$	15	A
	Pulsed (Note 2)	$I_{DM}$	60	A
Avalanche Current (Note 2)		$I_{AR}$	6.4	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	205	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.45	V/ns
Power Dissipation	TO-220/TO-263	$P_D$	250	W
	TO-220F		54	W
	TO-220F1/TO-220F2		52	W
	TO-247		312	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3.  $L=10\text{mH}$ ,  $I_{AS}=6.4\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$

4.  $I_{SD}\leq 15\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$ .

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-263	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-247		40	$^\circ\text{C}/\text{W}$
	TO-220/TO-263		0.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F	$\theta_{JC}$	2.3	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2		2.4	$^\circ\text{C}/\text{W}$
	TO-247		0.4	$^\circ\text{C}/\text{W}$

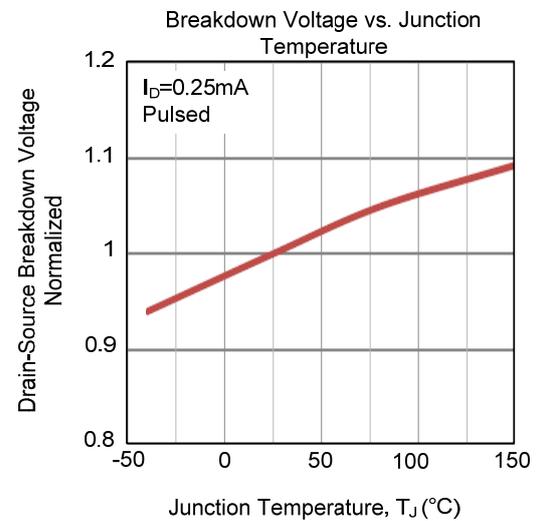
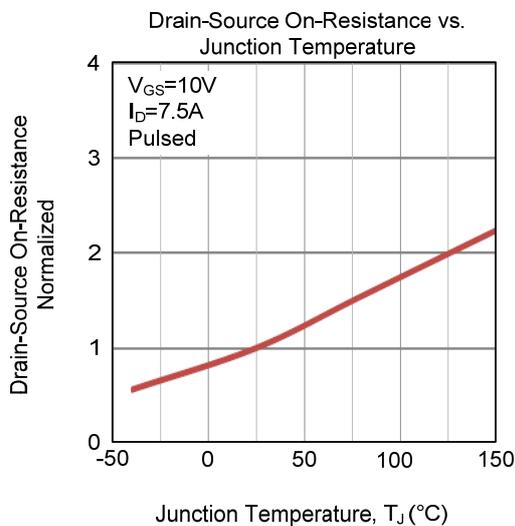
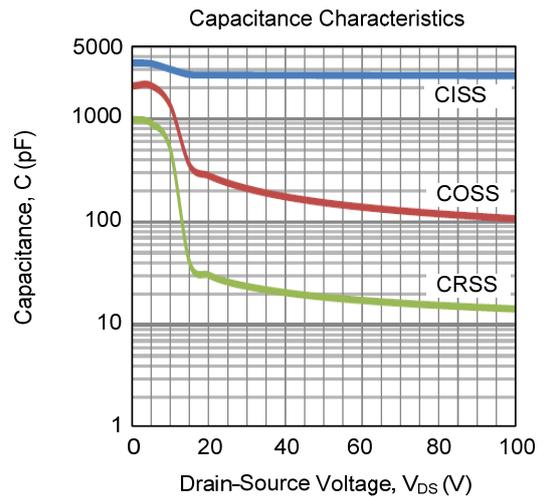
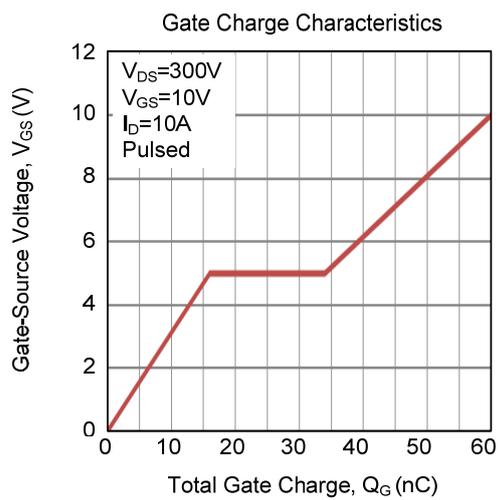
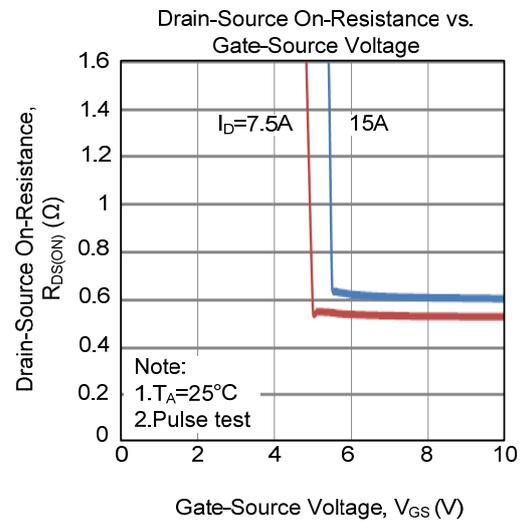
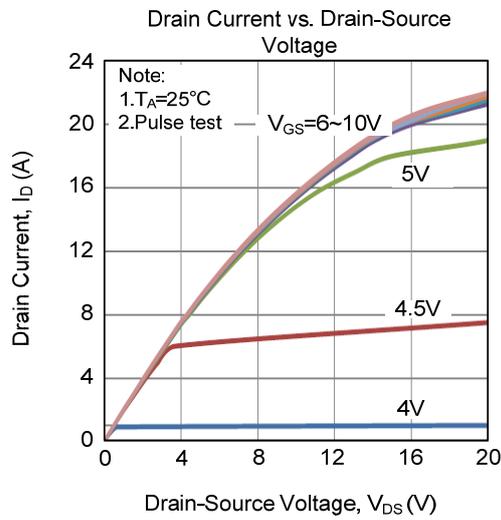
■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	650			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			1	μA
Gate- Source Leakage Current	Forward	I <sub>GSS</sub> V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V			+100	nA
	Reverse		V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0		4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =7.5A			0.65	Ω
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz		2700		pF
Output Capacitance	C <sub>OSS</sub>			240		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			26		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =300V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A, I <sub>G</sub> = 1mA (Note 1, 2)		60		nC
Gate-Source Charge	Q <sub>GS</sub>			16		nC
Gate-Drain Charge	Q <sub>GD</sub>			18		nC
Turn-ON Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =300V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A, R <sub>G</sub> =25Ω (Note 1, 2)		30		ns
Turn-ON Rise Time	t <sub>R</sub>			28		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			194		ns
Turn-OFF Fall Time	t <sub>F</sub>			43		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				15	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				60	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt=100A/μs		510		ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>				8.2	

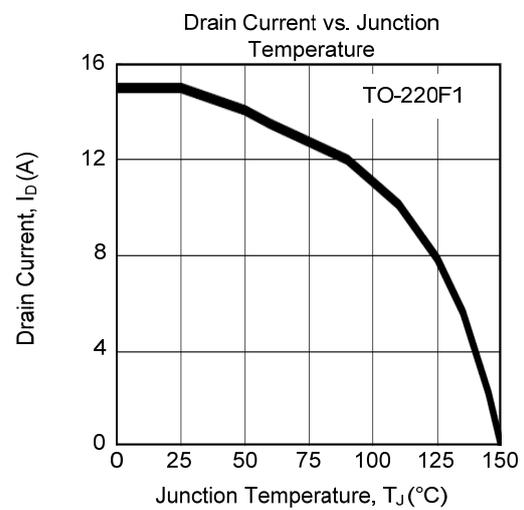
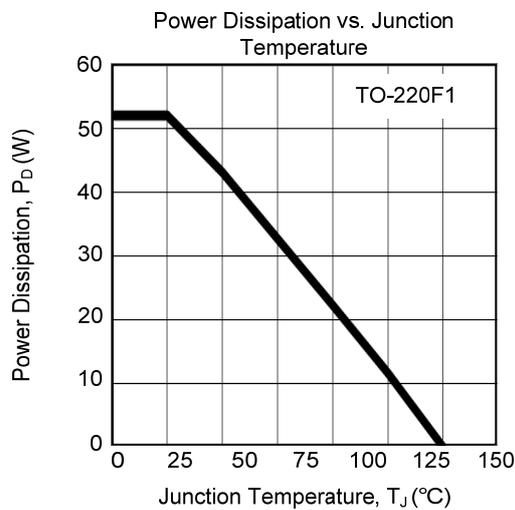
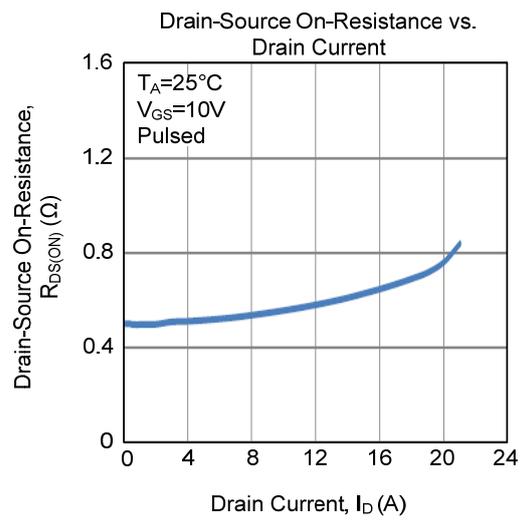
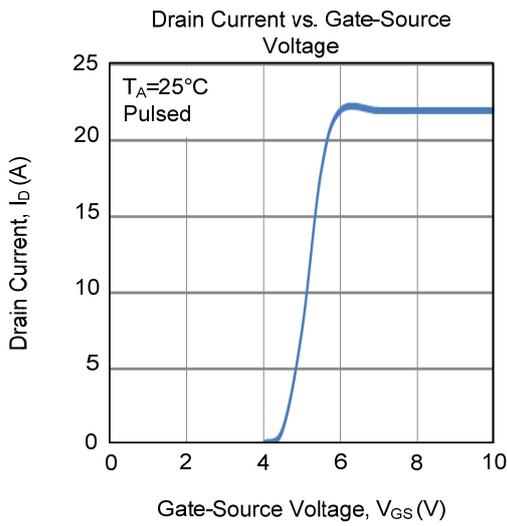
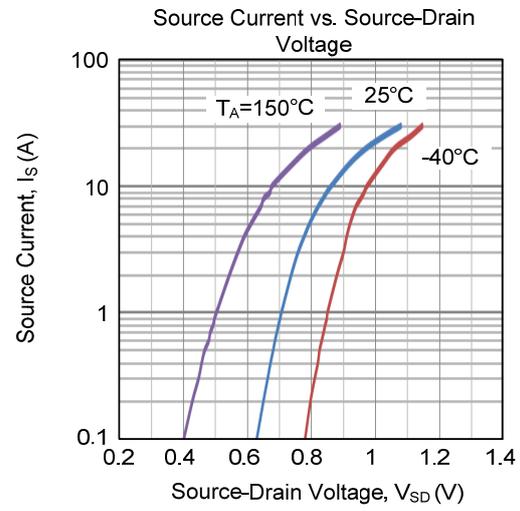
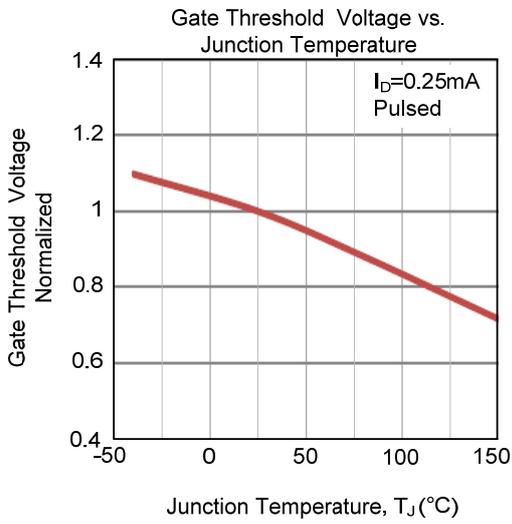
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

## TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)

